L	Hits	Search Text	DB	Time stamp
Number				
1	65	STI and buried and (interlayer with	USPAT;	2004/02/21
		dielectric) and plug and (doping or	US-PGPUB	10:03
		implantation or implanting) and memory		
2	65		USPAT;	2004/02/21
		dielectric) and plug and (doping or	US-PGPUB	10:11
		implantation or implanting) and memory)		
		and @ad<20030820		, , ,
3	0	STI and buried and (interlayer with	EPO; JPO;	2004/02/21
		dielectric) and plug and (doping or	DERWENT;	10:00
		implantation or implanting) and memory	IBM_TDB	
4	5	((STI and buried and (interlayer with	USPAT;	2004/02/21
		dielectric) and plug and (doping or	US-PGPUB	10:03
		implantation or implanting) and memory)		
	_	and @ad<20030820) and diode		2224/22/21
5	5	STI and buried and (interlayer with	USPAT;	2004/02/21
		dielectric) and plug and (doping or	US-PGPUB	10:04
	[implantation or implanting) and memory		
	l _	and diode	HCDAM	2004/02/21
6	5	(isolation with trench) and buried and	USPAT;	2004/02/21
		(interlayer with dielectric) and plug and	US-PGPUB	10:04
		(doping or implantation or implanting)		
_		and memory and diode	HCDAM.	2004/02/21
7	24	(isolation with trench) and (interlayer with dielectric) and plug and (doping or	USPAT; US-PGPUB	10:33
		implantation or implanting) and memory	OSFGFOB	10.33
		and diode		
8	19	((isolation with trench) and (interlayer	USPAT;	2004/02/21
°	1	with dielectric) and plug and (doping or	US-PGPUB	10:05
		implantation or implanting) and memory	00 10102	13733
ŀ		and diode) not ((isolation with trench)		
į		and buried and (interlayer with	1	
		dielectric) and plug and (doping or		
		implantation or implanting) and memory		
	İ	and diode)		
وا	19	(((isolation with trench) and (interlayer	USPAT;	2004/02/21
		with dielectric) and plug and (doping or	US-PGPUB	10:34
		implantation or implanting) and memory		
		and diode) not ((isolation with trench)		
		and buried and (interlayer with		1
	İ	dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode)) and @ad<20030820		0004/00/01
10	200	(STI or (isolation near3 trench)) and	USPAT;	2004/02/21
		(interlayer with dielectric) and (doping	US-PGPUB	11:10
		or implantation or implanting) and memory		
, ,	200	and bit and word ((STI or (isolation near3 trench)) and	USPAT;	2004/02/21
11	200		US-PGPUB	10:34
		(interlayer with dielectric) and (doping or implantation or implanting) and memory	35 13105	1 20.33
		and bit and word) and @ad<20030820		
12	150	(((STI or (isolation near3 trench)) and	USPAT;	2004/02/21
16	150	(interlayer with dielectric) and (doping	US-PGPUB	10:34
		or implantation or implanting) and memory		
		and bit and word) and Gad<20030820) not		
1		((STI and buried and (interlayer with		
		dielectric) and plug and (doping or		
		implantation or implanting) and memory)		
		and @ad<20030820)		

13	132	///(STI or /igolation near3 trench)) and	IISDAT ·	2004/02/21
13	132	((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implanting)	USPAT; US-PGPUB	2004/02/21 10:34
14	62	and memory and diode)) (((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) and plug	USPAT; US-PGPUB	2004/02/21 11:08
15	70	(((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) not (((((STI or (isolation near3 trench))) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not ((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) and plug and (memory and diode))) and plug)	USPAT; US-PGPUB	2004/02/21 10:53

16	31	(((((STI or (isolation near3 trench))	USPAT;	2004/02/21
		and (interlayer with dielectric) and	US-PGPUB	10:54
		(doping or implantation or implanting)		
		and memory and bit and word) and		
		@ad<20030820) not ((STI and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory) and @ad<20030820)) not		
		(((isolation with trench) and (interlayer		
		with dielectric) and plug and (doping or		
		implantation or implanting) and memory		1
		and diode) not ((isolation with trench)		
		and buried and (interlayer with		
		dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode))) not (((((STI or (isolation		
		near3 trench)) and (interlayer with		
		dielectric) and (doping or implantation		1
	1	or implanting) and memory and bit and		
		word) and @ad<20030820) not ((STI and		
		buried and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory) and		
		@ad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory and diode) not		
		((isolation with trench) and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory and diode))) and plug)) and		
		buried		

				2001/00/55
17	39	(((((STI or (isolation near3 trench))	USPAT;	2004/02/21
		and (interlayer with dielectric) and	US-PGPUB	11:08
		(doping or implantation or implanting)		
		and memory and bit and word) and		
		@ad<20030820) not ((STI and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory) and @ad<20030820)) not	4	
		(((isolation with trench) and (interlayer		
		with dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode) not ((isolation with trench)		
		and buried and (interlayer with		
		dielectric) and plug and (doping or implantation or implanting) and memory		
		and diode))) not (((((STI or (isolation		
		near3 trench)) and (interlayer with		
		dielectric) and (doping or implantation		
		or implanting) and memory and bit and		
		word) and @ad<20030820) not ((STI and		
		buried and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory) and		
		@ad<20030820)) not (((isolation with		
1	1	trench) and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory and diode) not		
		((isolation with trench) and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory and diode))) and plug)) not		
		((((((STI or (isolation near3 trench))		
		and (interlayer with dielectric) and		
		(doping or implantation or implanting)		
	ļ	and memory and bit and word) and		
	•	@ad<20030820) not ((STI and buried and		
ļ		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory) and @ad<20030820)) not		
		(((isolation with trench) and (interlayer		
		with dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode) not ((isolation with trench)		
		and buried and (interlayer with		
ļ		dielectric) and plug and (doping or		
	1	<pre>implantation or implanting) and memory and diode))) not (((((STI or (isolation)))))</pre>		
		near3 trench)) and (interlayer with		
1		dielectric) and (doping or implantation		
		or implanting) and memory and bit and		
		word) and @ad<20030820) not ((STI and		
		buried and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory) and		
		@ad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory and diode) not		
	ļ	((isolation with trench) and buried and]	
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
	1	and memory and diode))) and plug)) and		
		buried)	770	2004/02/21
18	0	(STI or (isolation near3 trench)) and	EPO; JPO;	2004/02/21
		(interlayer with dielectric) and (doping	DERWENT;	11:10
		or implantation or implanting) and memory	IBM_TDB	
		and bit and word	L	l